

N-channel 30 V 6.5 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 24 October 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	71	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	58	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	6.9	8.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	5.5	6.5	mΩ
Dynamic cl	naracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 15 \text{ V};$ see Figure 14; see Figure 15	-	2.6	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 15 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	9	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	- q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R0-30YLB	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	71	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	50	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; see Figure 4	-	283	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	58	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	210	-	V
Source-dra	ain diode				
Is	source current	T _{mb} = 25 °C	-	53	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$	-	283	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 71 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped; see Figure 3	-	13	mJ

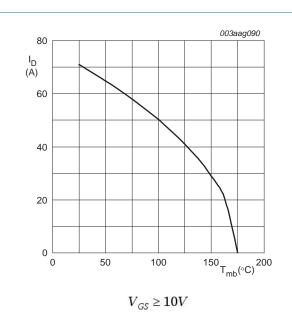


Fig 1. Continuous drain current as a function of mounting base temperature

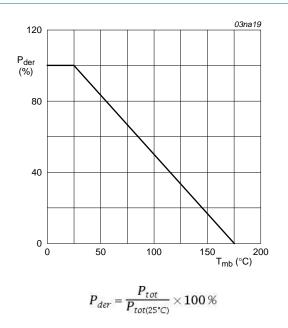
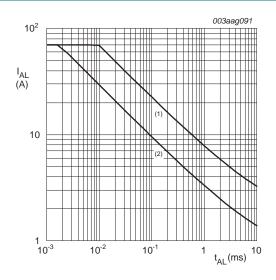


Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j \ (init)} = 25^{\circ}C$; (2) $T_{j \ (init)} = 100^{\circ}C$

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

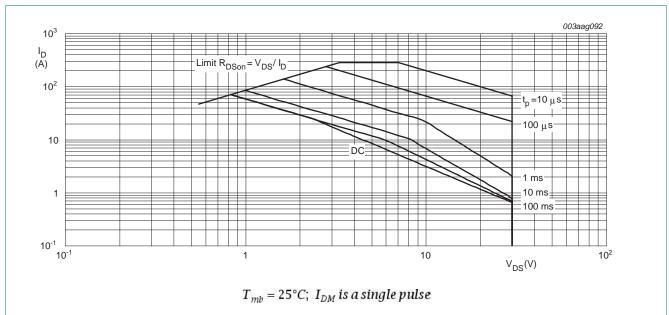
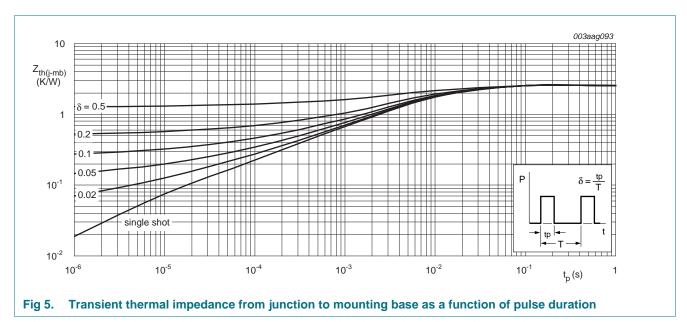


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.35	2.57	K/W



6. Characteristics

Table 6. Characteristics

iable 0.	Cital acteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.48	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V; } I_D = 20 \text{ A; } T_j = 25 \text{ °C; see}$ Figure 12	-	6.9	8.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	13.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	5.5	6.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	10.7	mΩ
R_G	gate resistance	f = 1 MHz	-	1.62	3.24	Ω
Dynamic	characteristics					
Q _{G(tot)} total gate charge	$I_D = 20 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	19	-	nC	
		$I_D = 20 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15	-	17	-	nC
Q_{GS}	gate-source charge	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	2.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.6	-	nC
Q_{GD}	gate-drain charge		-	2.6	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 20 \text{ A}$; $V_{DS} = 15 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.39	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1088	-	pF
Coss	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	278	-	pF
Crss	reverse transfer capacitance		-	78	-	pF
d(on)	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	16	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	15	-	ns
d(off)	turn-off delay time		-	29	-	ns

PSMN6R0-30YLB

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 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	7.2	-	nC
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 20 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.85	1.1	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	25.5	-	ns
Q_r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	15	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 20 \text{ A};$	-	15.9	-	ns
t _b	reverse recovery fall time	$dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{DS} = 15 \text{ V}$; see Figure 18	-	9.6	-	ns

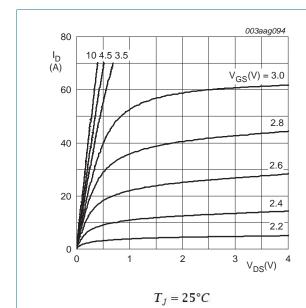
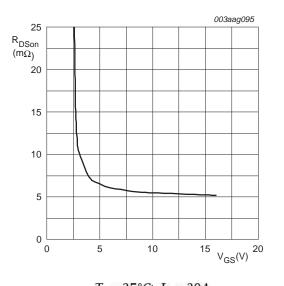


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 20A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

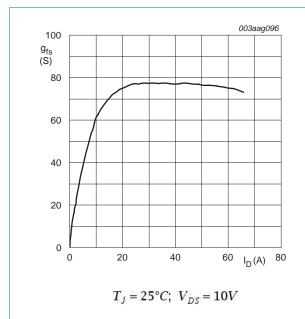


Fig 8. Forward transconductance as a function of drain current; typical values

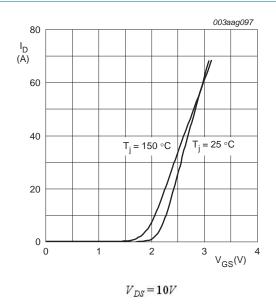


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

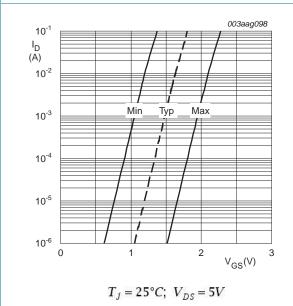


Fig 10. Sub-threshold drain current as a function of gate-source voltage

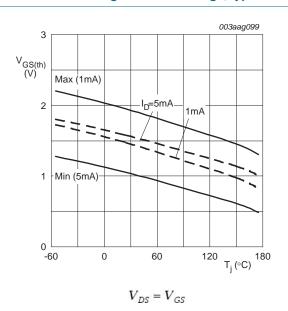


Fig 11. Gate-source threshold voltage as a function of junction temperature

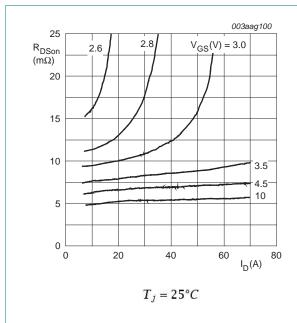


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

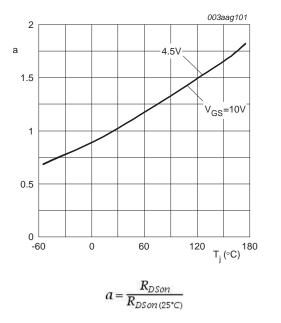


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

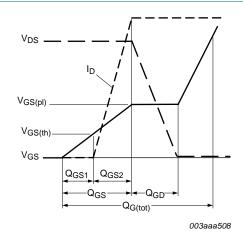
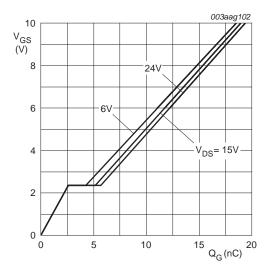


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 20A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

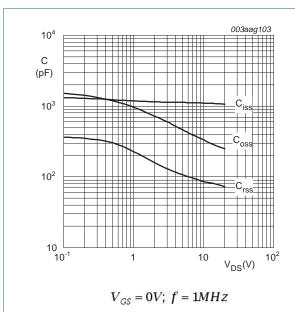


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

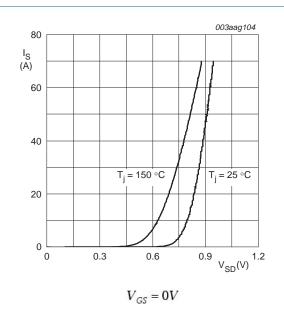


Fig 17. Source current as a function of source-drain voltage; typical values

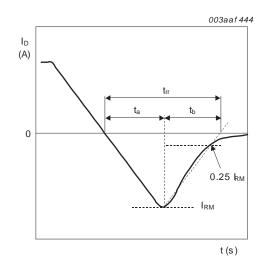
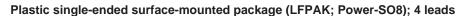
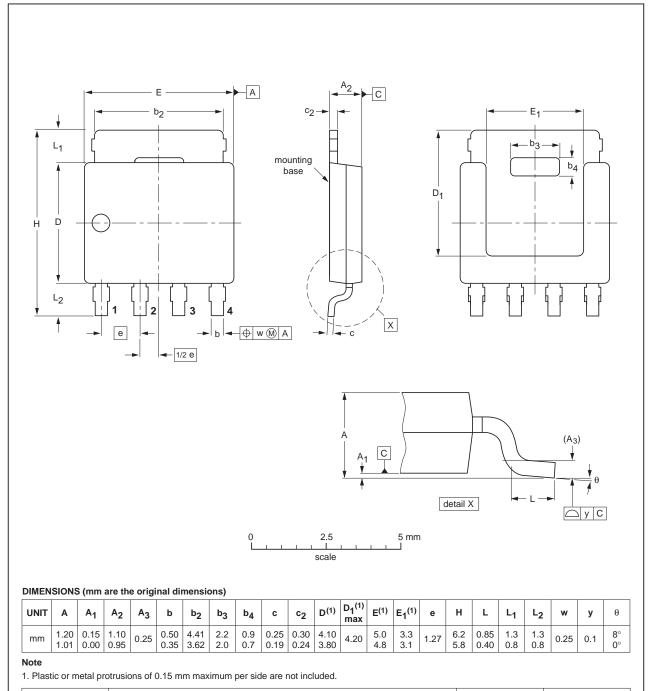


Fig 18. Reverse recovery timing definition

7. Package outline



SOT669



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT669		MO-235			06-03-16 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R0-30YLB v.2	20111024	Product data sheet	-	PSMN6R0-30YLB v.1
Modifications:	 Status changed fro 	m preliminary to product.		
	 Various changes to 	content.		
PSMN6R0-30YLB v.1	20110908	Preliminary data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history12
9	Legal information13
9.1	Data sheet status
9.2	Definitions13
9.3	Disclaimers
9.4	Trademarks14
10	Contact information14